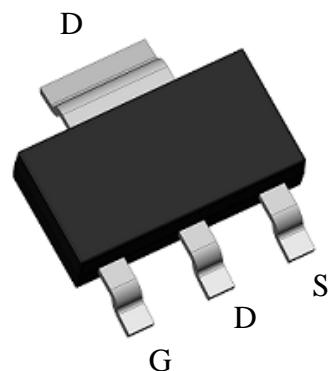


N-Channel Enhancement Mode MOSFET

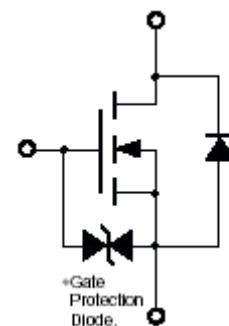
Features:

- Low Gate Charge
- Simple Drive Requirement
- ESD protected gate
- Pb-free lead plating & Halogen-free package

SOT-223



BV_{DSS}	100V
I_D @ V_{GS}=10V, T_A=25°C	3A
R_{DSON}@V_{GS}=10V, I_D=2A	109mΩ (typ.)



G : Gate D : Drain

S : Source

Ordering Information

Device	Package	Shipping
KWE100N10KRL3	SOT-223 (Pb-free lead plating & Halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings ($T_C=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current @ $T_A=25^\circ C$, $V_{GS}=10V$	I_D	3.0	A
Continuous Drain Current @ $T_A=70^\circ C$, $V_{GS}=10V$		2.4	
Pulsed Drain Current *1	I_{DM}	15	A
Avalanche Current @ $L=0.1mH$	I_{AS}	12	
Avalanche Energy @ $L=1mH$, $I_D=6A$, $V_{DD}=50V$ *2	E_{AS}	18	mJ
Repetitive Avalanche Energy @ $L=0.05mH$	E_{AR}	0.625	
Total Power Dissipation @ $T_A=25^\circ C$	P_D	2.5	W
Total Power Dissipation @ $T_A=70^\circ C$		1.6	
Operating Junction and Storage Temperature Range	T_j , T_{stg}	-55~+150	°C

Note : *1. Pulse width limited by maximum junction temperature

*2. Guaranteed by design, not by 100% test.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	18.5	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{\theta JA}$	50 (Note)	

Note : When mounted on a 1 in² pad of 2 oz. copper.

Characteristics ($T_C=25^\circ C$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	100	-	-	V	$V_{GS}=0V$, $I_D=250\mu A$
$V_{GS(th)}$	2	-	4		$V_{DS}=V_{GS}$, $I_D=250\mu A$
G_{FS} *1	-	1.9	-	S	$V_{DS}=10V$, $I_D=1A$
I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 16V$, $V_{DS}=0V$
I_{DSS}	-	-	1		$V_{DS}=80V$, $V_{GS}=0V$
	-	-	25		$V_{DS}=80V$, $V_{GS}=0V$, $T_j=125^\circ C$
$R_{DS(ON)}$ *1	-	109	140	mΩ	$V_{GS}=10V$, $I_D=2A$
Dynamic					
Q_g *1, 2	-	4.6	6.9	nC	$V_{DS}=80V$, $V_{GS}=10V$, $I_D=2A$
Q_{gs} *1, 2	-	1.5	2.3		
Q_{gd} *1, 2	-	1.5	2.3		
$t_{d(ON)}$ *1, 2	-	6	9	ns	$V_{DS}=50V$, $I_D=2A$, $V_{GS}=10V$, $R_G=1\Omega$
t_r *1, 2	-	16.8	25.2		
$t_{d(OFF)}$ *1, 2	-	13	19.5		
t_f *1, 2	-	5.6	8.4		

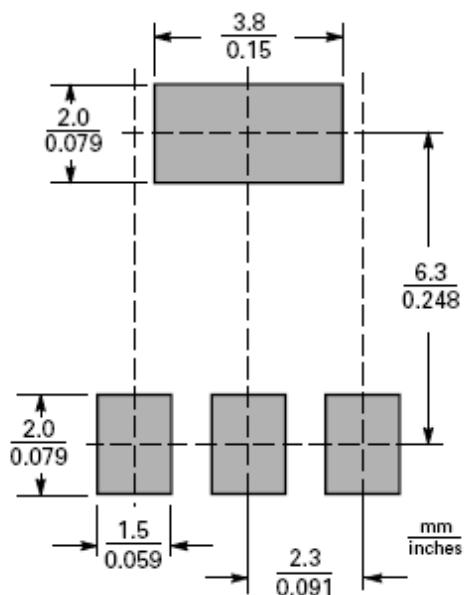
C _{iss}	-	263	395	pF	V _{GS} =0V, V _{DS} =50V, f=1MHz
C _{oss}	-	29	44		
C _{rss}	-	8	12		
Source-Drain Diode					
I _s *1	-	-	3	A	
I _{SM} *3	-	-	15		
V _{SD} *1	-	0.83	1.2	V	I _s =2A, V _{GS} =0V
t _{rr}	-	17.2	-	ns	I _F =2A, dI _F /dt=100A/μs
Q _{rr}	-	13.5	-	nC	

Note : *1.Pulse Test : Pulse Width \leq 300μs, Duty Cycle \leq 2%

*2.Independent of operating temperature

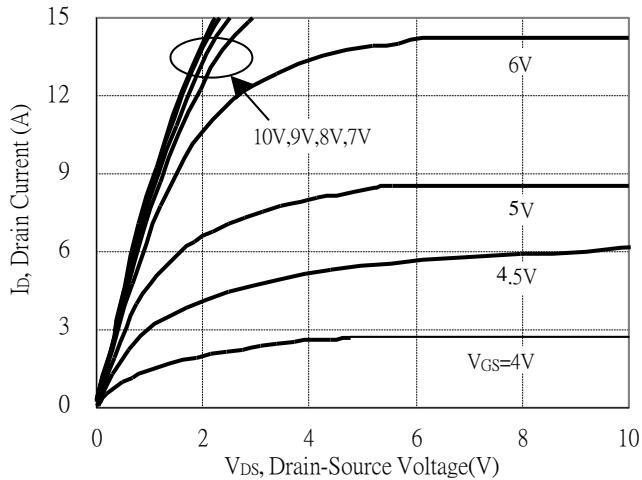
*3.Pulse width limited by maximum junction temperature.

Recommended soldering footprint

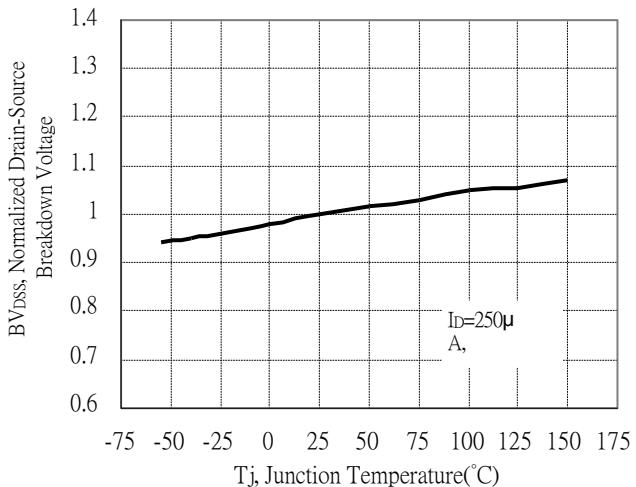


Typical Characteristics

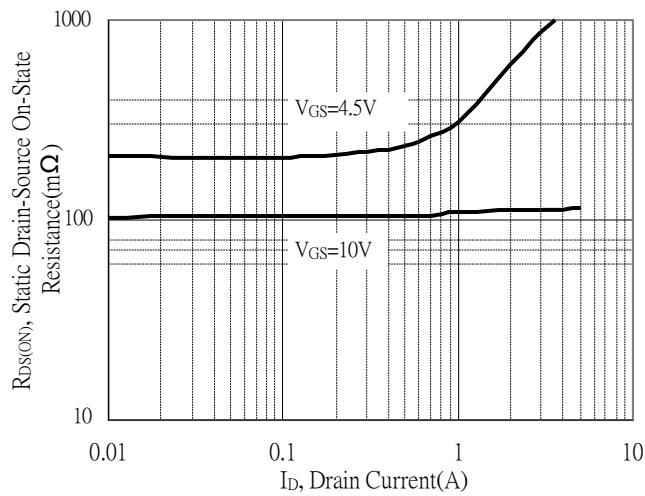
Typical Output Characteristics



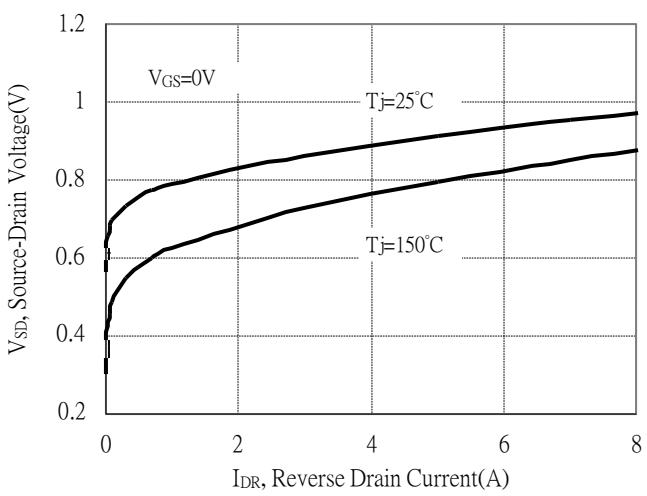
Breakdown Voltage vs Junction Temperature



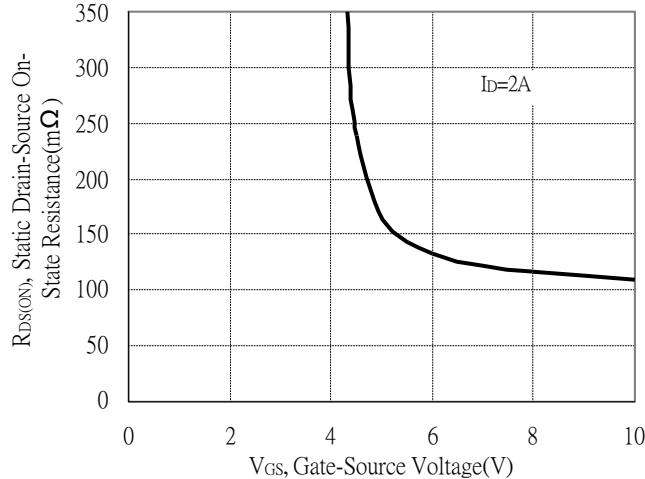
Static Drain-Source On-State resistance vs Drain Current



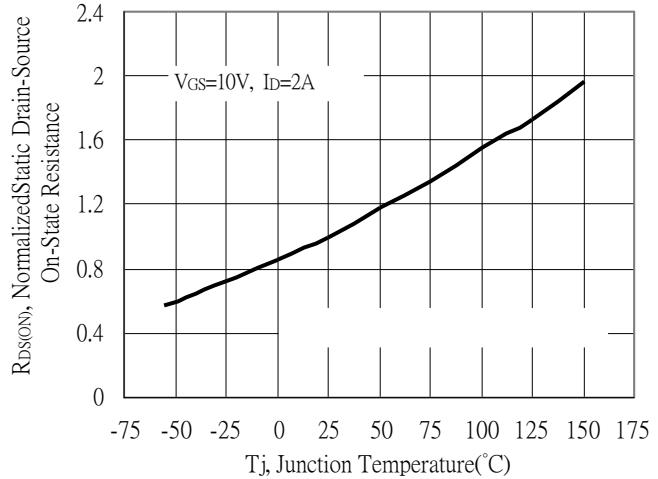
Reverse Drain Current vs Source-Drain Voltage



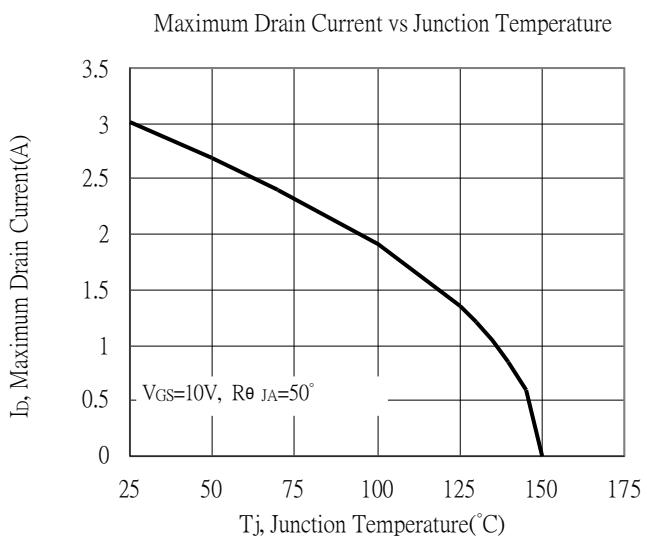
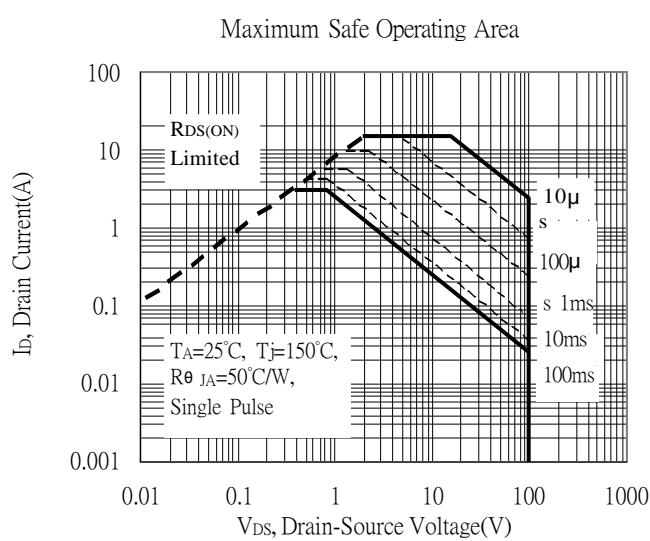
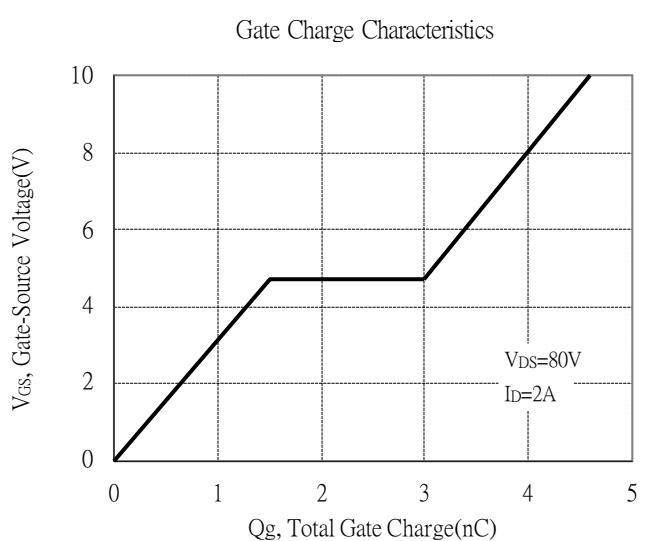
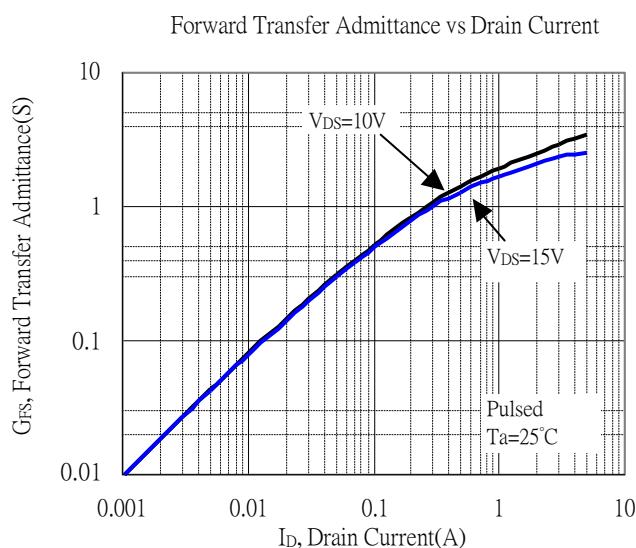
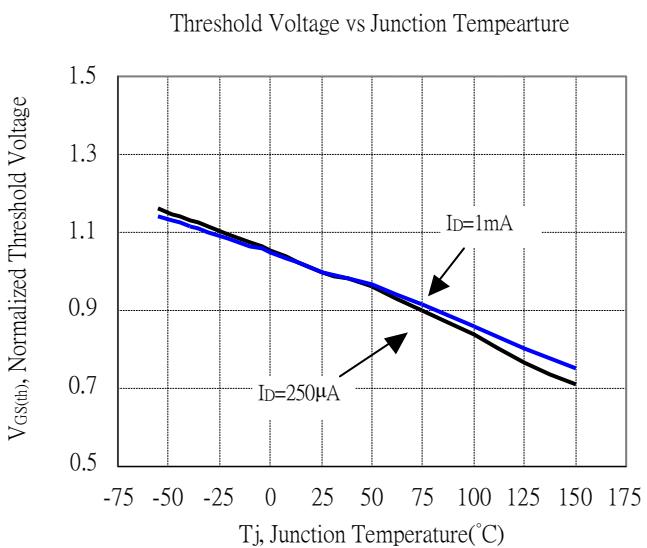
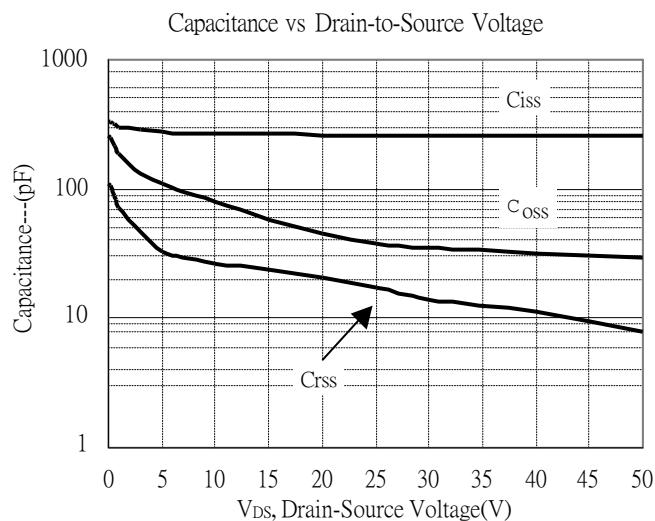
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Drain-Source On-State Resistance vs Junction Temperature

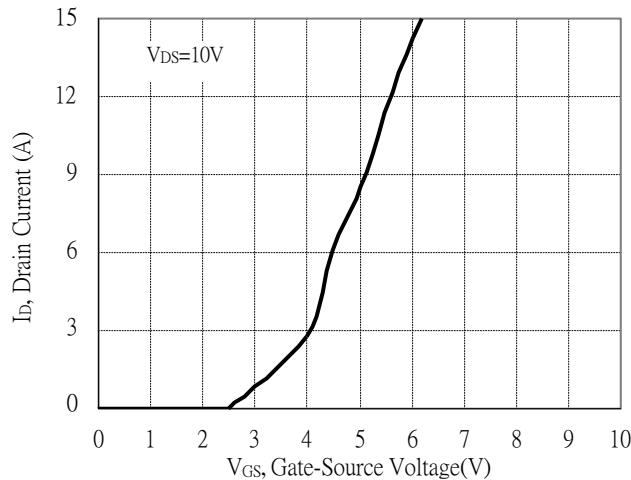


Typical Characteristics(Cont.)

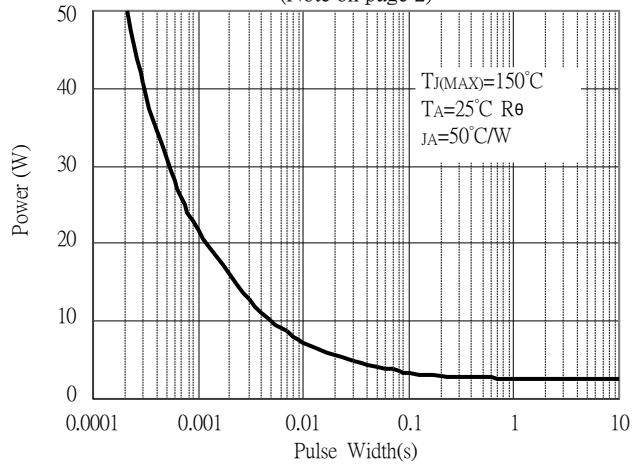


Typical Characteristics(Cont.)

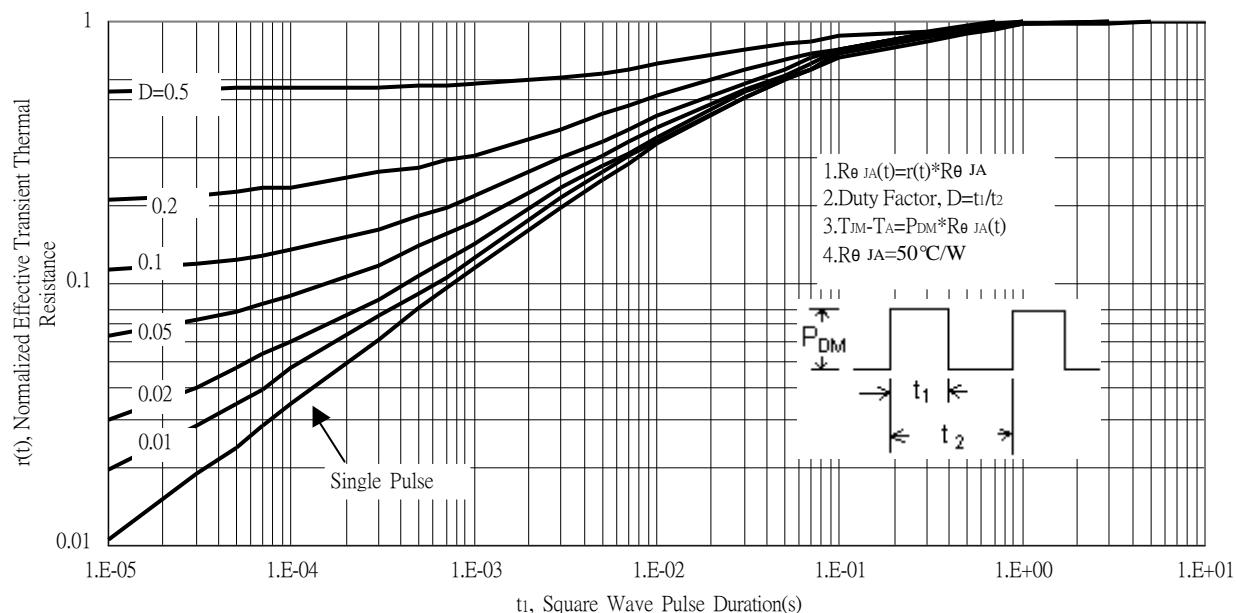
Typical Transfer Characteristics



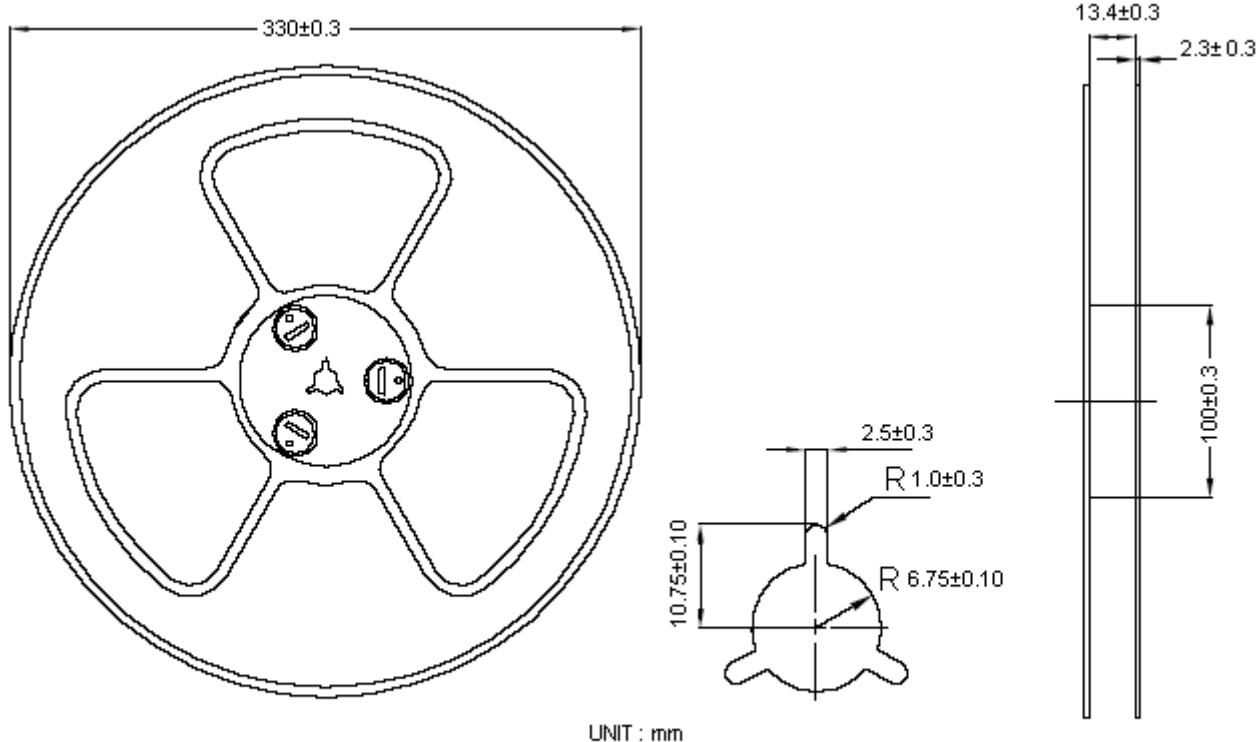
Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



Transient Thermal Response Curves



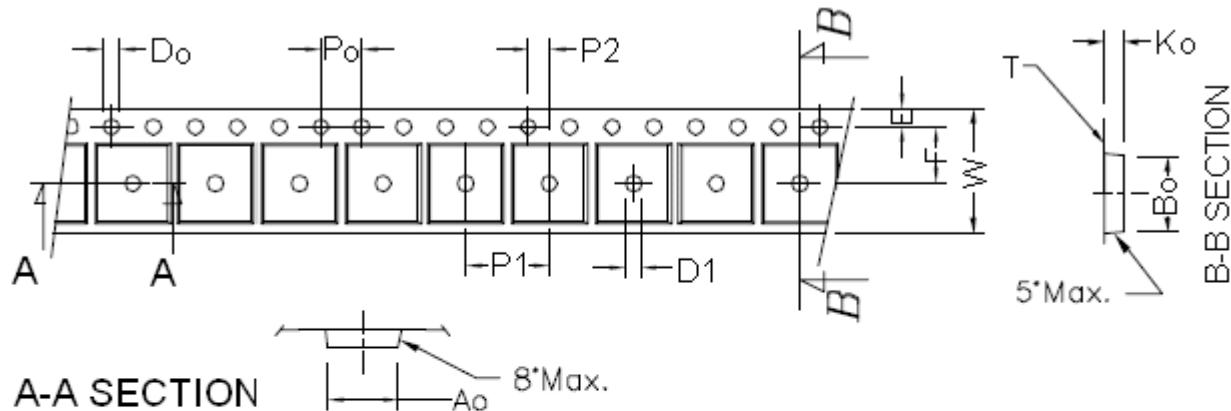
Reel Dimension



UNIT : mm

NOTE : 1. Material : Anti-static polystyrene
 2. Surface resistivity $10^9 \Omega/\text{sq}$

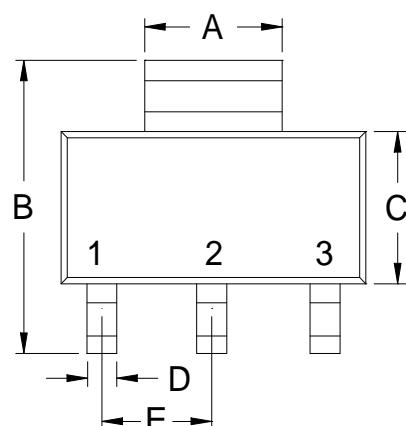
Carrier Tape Dimension



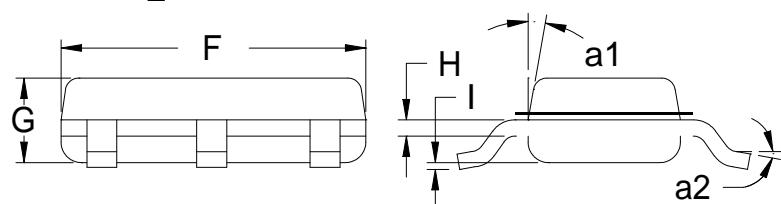
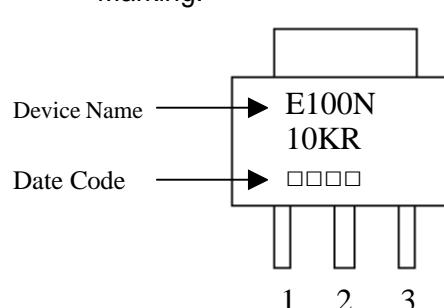
Symbol	Ao	Bo	Ko	Po	P1	P2	T
Spec	6.83±0.1	7.42±0.1	1.88±0.1	4.0±0.1	8.0±0.10	2.0±0.05	0.292±0.02
Symbol	E	F	Do	D1	W	10Po	
Spec	1.75±0.1	5.5±0.05	1.60±0.1	1.5±0.25	12 ^{+0.3} -0.1	40.0±0.2	

Unit : mm

SOT-223 Dimension



Marking:



Style: Pin 1.Gate 2.Drain 3.Source

3-Lead SOT-223 Plastic
Surface Mounted Package
Package Code: L3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.23	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					